

# InP S dope 4" wafer



Prameter	Customer's Requirements		UOM
Material	InP		
Growth Method	VGF		
Conduct Type	S-C-N		
Dopant	S		
Diameter	100±0.5		mm
Orientation	(100)±0.5°		
Orientation Angle	N/A		
OF Location/Length	[0-1 1]±0.5 /32.5±1		
IF Location/Length	[0-11]±0.5 / 18±1		
Ingot CC	Min: 1.00E+18	Max: 6.00E+18	/cm <sup>3</sup>
Resistivity	Min: N/A	Max: N/A	Ω.cm
Mobility	Min: N/A	Max: N/A	/cm <sup>2</sup> /v.s
EPD	Min: N/A	Max: 500	/cm <sup>2</sup>
Thickness	Min: 600	Max: 650	μm
Edge Rounding	N/A		mmR
Laser Marking	N/A		
TTV/TIR	Max: 10		μm
BOW	Max: 10		μm
Warp	Max: 15		μm
Surface Finish-front	Polished		
Surface Finish-Back	Diamond ground and etched		
Partical Count	N/A		
Epi-Ready	N/A		